



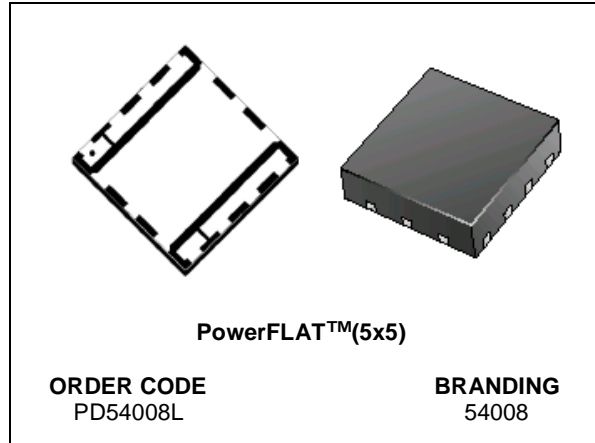
# PD54008L

## RF POWER TRANSISTORS The *LdmoST* PLASTIC FAMILY

TARGET DATA

### N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

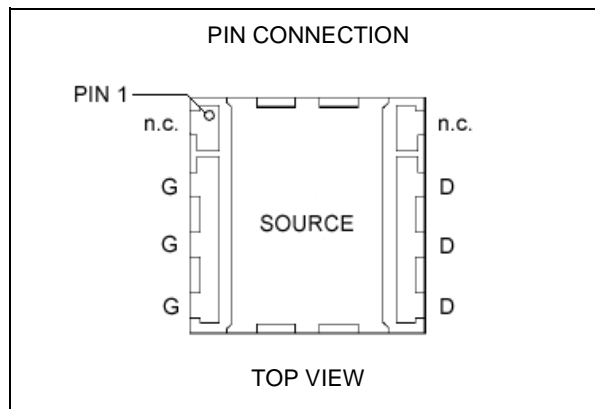
- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- P<sub>OUT</sub> = 8 W WITH 19 dB gain @ 500 MHz
- NEW LEADLESS PLASTIC PACKAGE
- ESD PROTECTION
- SUPPLIED IN TAPE & REEL OF 3K UNITS



### DESCRIPTION

The PD54008L is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 7 V in common source mode at frequencies of up to 1 GHz. PD54008L boasts the excellent gain, linearity and reliability of STH1LV latest LDMOS technology mounted in the innovative leadless SMD plastic package, PowerFLAT™.

PD54008L's superior linearity performance makes it an ideal solution for portable radio.



### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25 °C)

Symbol	Parameter	Value	Unit
V <sub>(BR)DSS</sub>	Drain-Source Voltage	25	V
V <sub>GS</sub>	Gate-Source Voltage	-0.5 to +15	V
I <sub>D</sub>	Drain Current	4	A
P <sub>DISS</sub>	Power Dissipation (@ T <sub>c</sub> = 70°C)	44	W
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

### THERMAL DATA

R <sub>th(j-c)</sub>	Junction -Case Thermal Resistance	1.8	°C/W
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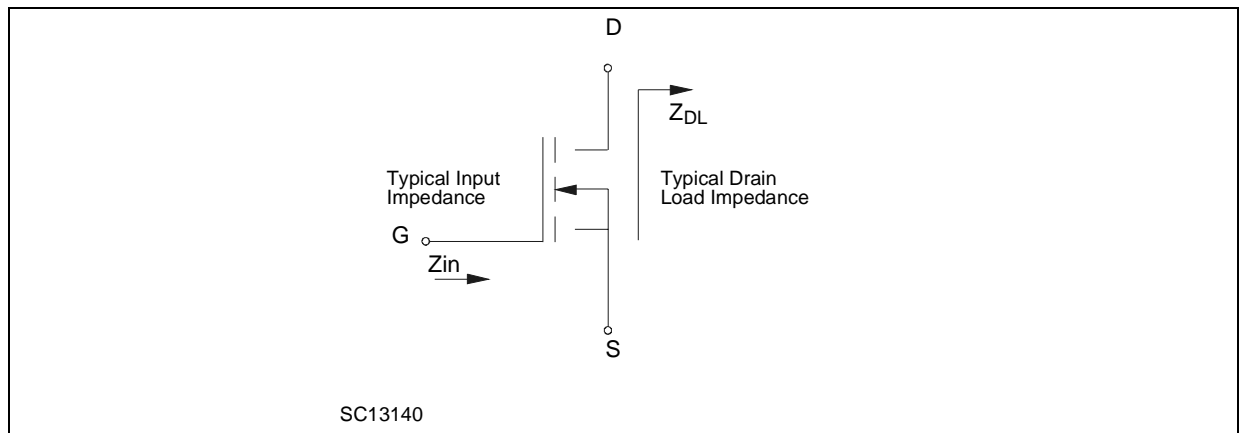
## ELECTRICAL SPECIFICATION (T<sub>CASE</sub> = 25 °C)

### STATIC (Per Section)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V			1	μA
I <sub>GSS</sub>	V <sub>GS</sub> = 20 V	V <sub>DS</sub> = 0 V			1	μA
V <sub>GS(Q)</sub>	V <sub>DS</sub> = 10 V	I <sub>D</sub> = 50 mA	2.0		5.0	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 0.5 A		0.13	0.16	V
g <sub>FS</sub>	V <sub>DS</sub> = 10 V	I <sub>D</sub> = 3.2 A		TBD		mho
C <sub>ISS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 7.5 V		54		pF
C <sub>OSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 7.5 V		43		pF
C <sub>RSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 7.5 V		4.0		pF

### DYNAMIC

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
P <sub>OUT</sub>	V <sub>DD</sub> = 7.5 V	I <sub>DQ</sub> = 150 mA	8			W
G <sub>PS</sub>	V <sub>DD</sub> = 7.5 V	I <sub>DQ</sub> = 150 mA	16	19		dB
η <sub>D</sub>	V <sub>DD</sub> = 7.5 V	I <sub>DQ</sub> = 150 mA	50	55		%
Load mismatch	V <sub>DD</sub> = 9.5 V	I <sub>DQ</sub> = 150 mA	20:1			VSWR



### ESD PROTECTION CHARACTERISTICS

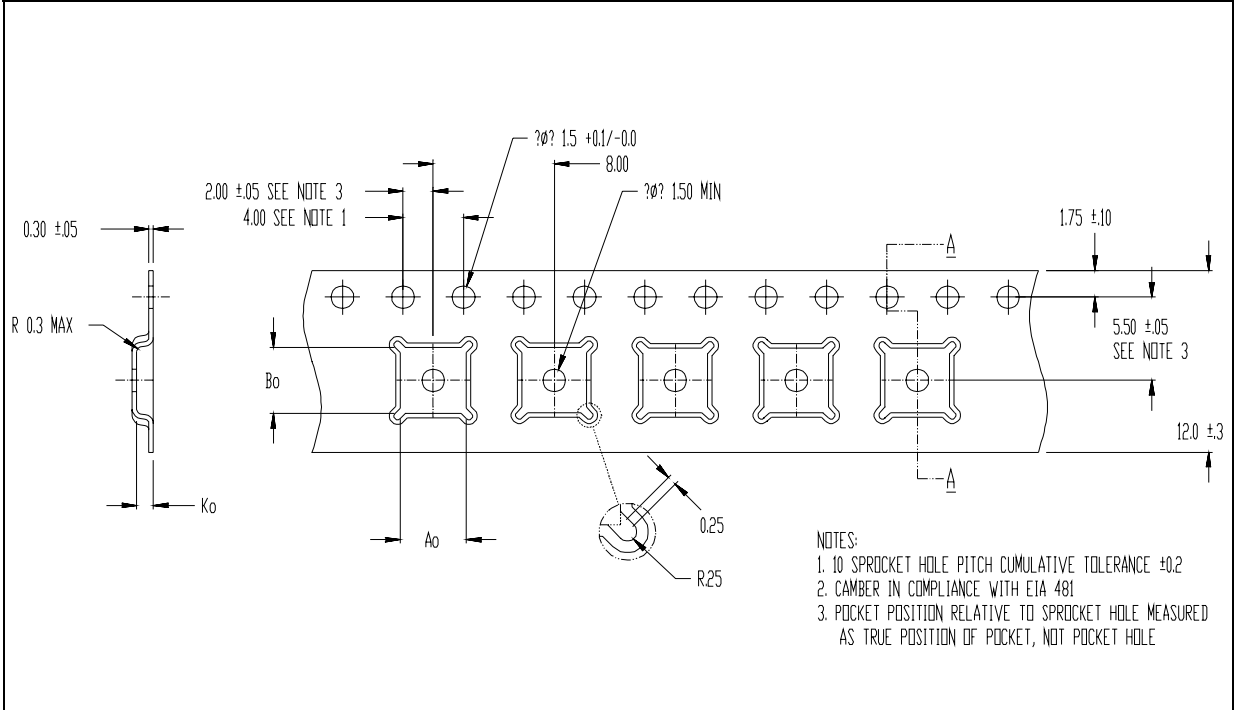
Test Conditions	Class
Human Body Model	2
Machine Model	M3

### MOISTURE SENSITIVITY LEVEL

Test Methodology	Rating
J-STD-020B	MSL 3

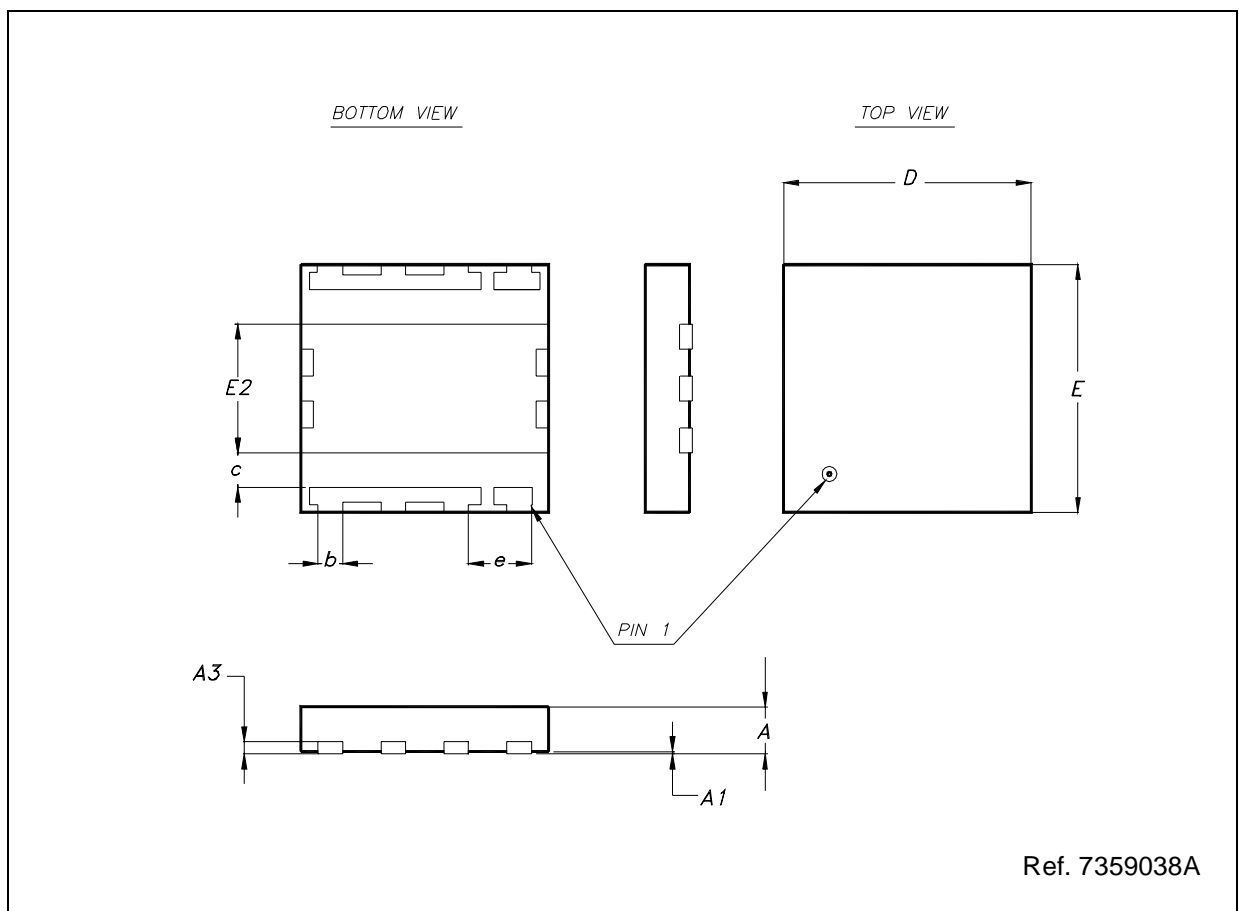
TAPE & REEL DIMENSIONS

	mm		
	MIN.	TYP.	MAX
Ao	5.15	5.25	5.35
Bo	5.15	5.25	5.35
Ko	1.0	1.1	1.2



**PowerFLAT™ MECHANICAL DATA**

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A		0.90	1.00		0.035	0.039
A1		0.02	0.05		0.001	0.002
A3		0.24			0.009	
b	0.43	0.51	0.58	0.017	0.020	0.023
c	0.64	0.71	0.79	0.025	0.028	0.031
D		5.00			0.197	
E		5.00			0.197	
E2	2.49	2.57	2.64	0.098	0.101	0.104
e		1.27			0.050	



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